

L Number	Hits	Search Text	DB	Time stamp
-	1	((("6355561") or ("6365486"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:35
-	4817	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 09:50
-	81048	heated same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:17
-	246	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:17
-	154585	precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:17
-	75	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)) and precursor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:17
-	37078	carrier adj gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:18
-	36	((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale) and (heated same substrate)) and precursor) and (carrier adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:30
-	3	("5916365").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:55
-	3	("4058430").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/27 14:55
-	233	tungsten adj hexafluoride and silicon adj wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:16
-	20738	second adj temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 09:52
-	2	hexamethyldisilazne	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:19
-	5749	hexamethyldisilazane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:19

-	1	(tungsten adj hexafluoride and silicon adj wafer) and hexamethyldisilazane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:27
-	1115557	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:28
-	205	(tungsten adj hexafluoride and silicon adj wafer) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:45
-	3	("5225366").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 14:45
-	8	5225366.URPN.	USPAT	2002/03/28 14:52
-	5	5294286.URPN.	USPAT	2002/03/28 15:03
-	0	5503105.URPN.	USPAT	2002/03/28 15:05
-	15	("4058430"   "4389973"   "4767494"   "4845049"   "4859627"   "4876218"   "4993357"   "5060595"   "5071670"   "5130269"   "5166092"   "5225366"   "5256244"   "5270247"   "5693139").PN.	USPAT	2002/03/28 15:06
-	15	heated adj wafer adj chuck	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/31 14:57
-	39	semiconductor adj wafer and chuck and heat and cool and robotic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/31 14:59
-	5233	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:20
-	41	second adj temperature and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/30 09:53
-	4	5130269.URPN.	USPAT	2002/08/30 09:56
-	0	micron.as. and (chemiabsorb or chemiabsorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:13
-	9	micron.as. and (chemisorb or chemisorbing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:14
-	6894	(atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:30

-	0	nh2 and h2o and ((atomic adj layer adj deposition) or (atomic adj layer adj epitaxy) or ald or ale )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 09:30
-	128	precursor adj gas and ald	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/07 11:16
-	10	((("6627260") or ("5937300") or ("6060383") or ("6258690") or ("6596636")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:28
-	236	(438/628).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:36
-	12	(ald or atomic adj layer adj deposition) and ((438/628).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:51
-	3851	(ald or atomic adj layer adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:51
-	1158	(metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
-	315	activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
-	255	agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition) )))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53
-	32	semiconductor and (agent and (activation and ((metal adj halide or metal adj organic or alcohol or carboxylic adj acid or amine) and ((ald or atomic adj layer adj deposition) ))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 13:53